



30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max Tc = +25°C
	11mΩ @ V _{GS} = 10V	30A
30V	$13m\Omega$ @ $V_{GS} = 4.5V$	25A

Features and Benefits

- Ultra Low Gate Threshold Voltage
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- ESD Protected Gate
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description and Applications

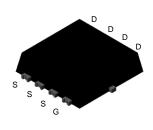
This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

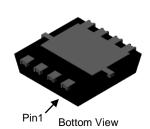
Mechanical Data

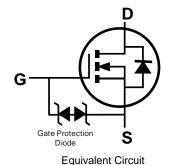
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.03 grams (Approximate)





Top View





Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3009UFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMT3009UFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

PowerDI3333-8 (SWP) (Type UX)

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- $4. For packaging details, go to our website at \ https://www.diodes.com/design/support/packaging/diodes-packaging/.$

Marking Information



SH3 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week Code (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	30	V	
Gate-Source Voltage	Vgss	±12	V	
	$T_A = +25$ °C $T_A = +70$ °C	I _D	10.6 8.5	А
Continuous Drain Current V _{GS} = 10V (Note 7)	$T_C = +25$ °C $T_C = +70$ °C	lo	30 25	А
Maximum Continuous Body Diode Forward Current (Note 7)	Is	2.1	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	80	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	Ism	80	Α	
Avalanche Current, L = 0.1mH (Note 8)	las	19	A	
Avalanche Energy, L = 0.1mH (Note 8)	Eas	18	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	105.2	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	PD	2.6	W
Thermal Resistance, Junction to Case (Note 6)	Steady State	RθJA	48.2	°C/W
Thermal Resistance, Junction to Case (Note 7)	Steady State	R ₀ JC	3.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

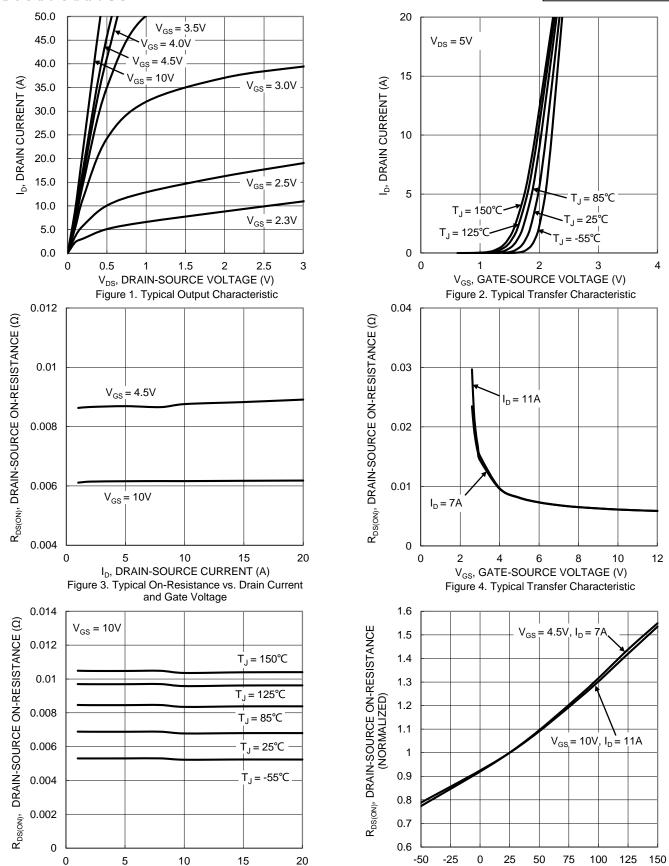
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(TH)	0.5	_	1.8	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	8.6	11	mΩ	$V_{GS} = 10V, I_D = 11A$	
Static Drain-Source On-Resistance	RDS(ON)	_	11.5	13		$V_{GS} = 4.5V, I_{D} = 7A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	V _{GS} = 0V, I _S = 8.8A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	894	_	pF	\	
Output Capacitance	Coss	_	381	_	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	76	_	pF	I = I.UIVIDZ	
Gate Resistance	R_g	_	1.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (VGS = 10V)	Qg	_	14.6	_		V _{DS} = 15V, I _D = 10A	
Total Gate Charge (VGS = 4.5V)	Qg	_	7.4	_	nC		
Gate-Source Charge	Qgs	_	1.6	_	IIC		
Gate-Drain Charge	Q_{gd}	_	3.4	_			
Turn-On Delay Time	t _{D(ON)}	_	3.4	_		$\begin{aligned} &V_{GS}=10V,V_{DD}=15V,R_g=1\Omega,\\ &I_{D}=8.8A \end{aligned}$	
Turn-On Rise Time	t _R	_	5.5	_			
Turn-Off Delay Time	tD(OFF)	_	9.6	_	ns		
Turn-Off Fall Time	t _F	_	1.6	_			
Body Diode Reverse Recovery Time	trr	_	17	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	6.7	_	nC	I _F = 10A, dI/dt = 100A/μs	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







I_D, DRAIN CURRENT (A)

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

 T_J , JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with Junction

Temperature





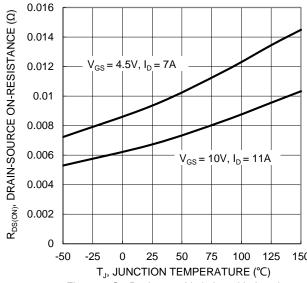


Figure 7. On-Resistance Variation with Junction Temperature

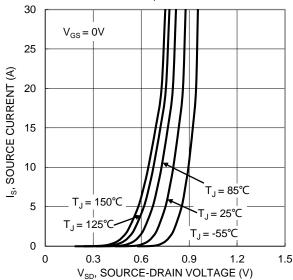
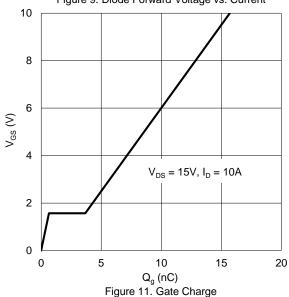


Figure 9. Diode Forward Voltage vs. Current



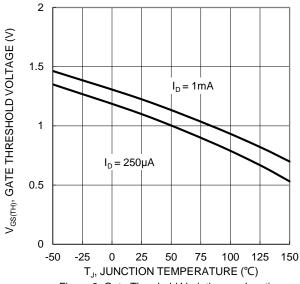
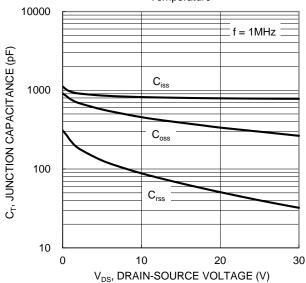
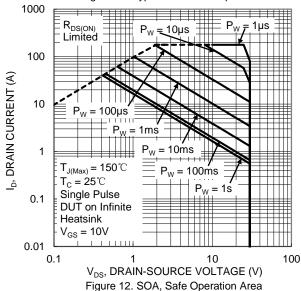


Figure 8. Gate Threshold Variation vs. Junction Temperature



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance



May 2020

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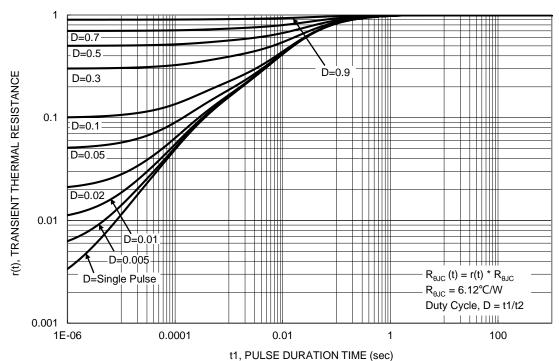


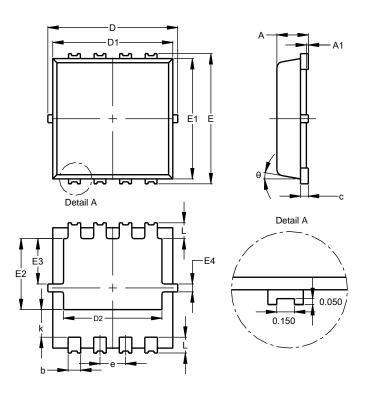
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

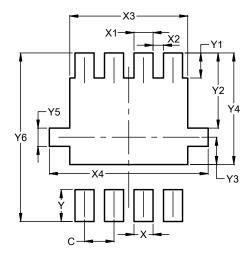


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min Max Typ				
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15 3.0			
E2	1.60	0 2.00 1.80			
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	_	_	0.65		
k	0.50	0.90	0.70		
┙	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
Х3	2.600			
X4	3.500			
Υ	0.700			
Y1	0.550			
Y2	1.650			
Y3	0.600			
Y4	2.450			
Y5	0.400			
Y6	3.700			



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